

88D D 8235605 0014912 6 SIEG

88D 14912 D T-39-13

BUZ 213

SIEMENS AKTIENGESELLSCHAFT

Main ratings

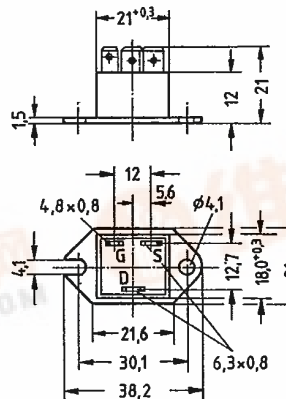
Drain-source voltage $V_{DS} = 500$ V
Continuous drain current $I_D = 8,5$ A
Drain-source on-resistance $R_{DS(on)} = 0,6 \Omega$

N-Channel



Description FREDET with fast-recovery reverse diode, N-channel, enhancement mode
Case Plastic package TO 238 AA with insulated metal base plate in accordance with JEDEC, compatible with TO 3; AMP plug-in connections.
Approx. weight 21 g

Type	Ordering code
BUZ 213	C67078-A1700-A2



Dimensions in mm

Maximum ratings

Description	Symbols	Ratings	Units	Conditions
Drain-source voltage	V_{DS}	500	V	
Drain-gate voltage	V_{DGR}	500	V	$R_{GS} = 20 \text{ k}\Omega$
Continuous drain current	I_D	8,5	A	$T_C = 25^\circ \text{C}$
Pulsed drain current	I_{Dpuls}	34	A	$T_C = 25^\circ \text{C}$
Gate-source voltage	V_{GS}	± 20	V	
Max. power dissipation	P_D	83,3	W	$T_C = 25^\circ \text{C}$
Operating and storage temperature range	T_{stg}	$-40 \dots +150$	$^\circ \text{C}$	
Isolation test voltage	V_{is}	3500	Vdc ¹⁾	$t = 1 \text{ min}$
DIN humidity category		F	-	DIN 40040
IEC climatic category		40/150/56	-	DIN IEC 68-1

Thermal resistance

Chip - case $R_{thJC} \leq 1,5$ K/W

¹⁾ Isolation test voltage between drain and base plate referred to standard climate 23/50 in accordance with DIN 50014.

88D D ■ 8235605 0014913 8 ■ SIEG

88D 14913 D T-39-13

BUZ 213

SIEMENS AKTIENGESSELLSCHAF

Electrical characteristics(at $T_j = 25^\circ\text{C}$ unless otherwise specified)

Description	Symbol	Characteristics			Unit	Conditions
		min.	typ.	max.		
Static ratings						
Drain-source breakdown voltage	$V_{(BR)DSS}$	500	—	—	V	$V_{GS} = 0V$ $I_D = 0,25mA$
Gate threshold voltage	$V_{GS(th)}$	2,1	3,0	4,0		$V_{DS} = V_{GS}$ $I_D = 1mA$
Zero gate voltage drain current	I_{DSS}	—	20 100	250 1000	μA	$T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$ $V_{DS} = 500V$ $V_{GS} = 0V$
Gate-source leakage current	I_{GSS}	—	10	100	nA	$V_{GS} = 20V$ $V_{DS} = 0V$
Drain-source on-resistance	$R_{DS(on)}$	—	0,55	0,6	Ω	$V_{GS} = 10V$ $I_D = 5,5A$
Dynamic ratings						
Forward transconductance	g_{fs}	2,7	5,3	—	S	$V_{DS} = 25V$ $I_D = 5,5A$
Input capacitance	C_{iss}	—	3,8	4,9	nF	$V_{GS} = 0V$
Output capacitance	C_{oss}	—	250	400	pF	$V_{DS} = 25V$ $f = 1MHz$
Reverse transfer capacitance	C_{rss}	—	100	170		
Turn-on time t_{on} ($t_{on} = t_{d(on)} + t_r$)	$t_{d(on)}$	—	50	75	ns	$V_{CC} = 30V$ $I_D = 2,8A$ $V_{GS} = 10V$ $R_{GS} = 50\Omega$
	t_r	—	80	120		
Turn-off time t_{off} ($t_{off} = t_{d(off)} + t_f$)	$t_{d(off)}$	—	330	430		
	t_f	—	110	140		
Fast-recovery reverse diode						
Continuous reverse drain current	I_{DR}	—	—	8,5	A	$T_C = 25^{\circ}C$
Pulsed reverse drain current	I_{DRM}	—	—	34		
Diode forward on-voltage	V_{SD}	—	1,3	1,7	V	$I_F = 2 \times I_{DR}$ $V_{GS} = 0V, T_J = 25^{\circ}C$
Reverse recovery time	t_{rr}	—	180 — 220	250 300	ns	$T_J = 25^{\circ}C$ $T_J = 150^{\circ}C$ $I_F = I_{DR}$ $di/dt = 100A/\mu s$ $V_R = 100V$
Reserve recovery charge	Q_{rr}	—	0,65 — 2,6	1,2 5,0		
Repetitive peak reverse current	I_{RRM}	—	— 15	—	A	$T_J = 25^{\circ}C$ $T_J = 150^{\circ}C$

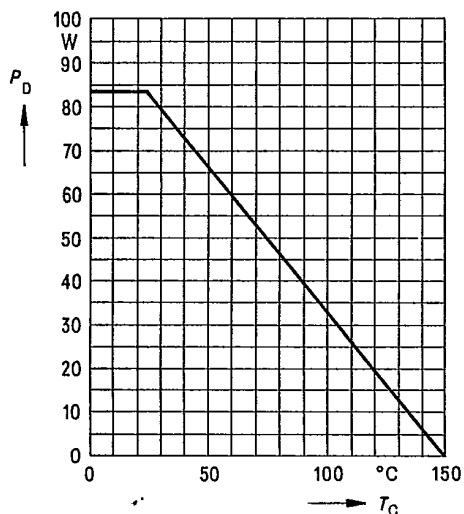
88D D ■ 8235605 0014914 T ■ SIEG

88D 14914 D T-39-13

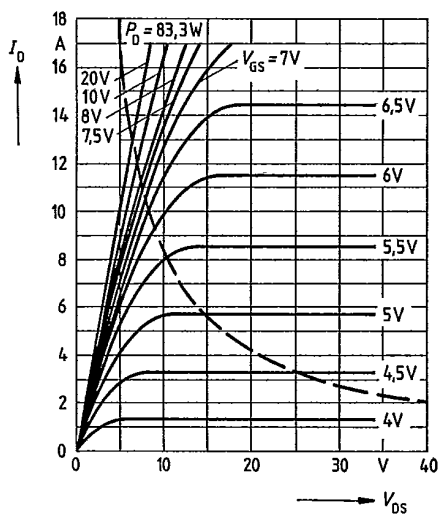
BUZ 213

SIEMENS AKTIENGESELLSCHAFT

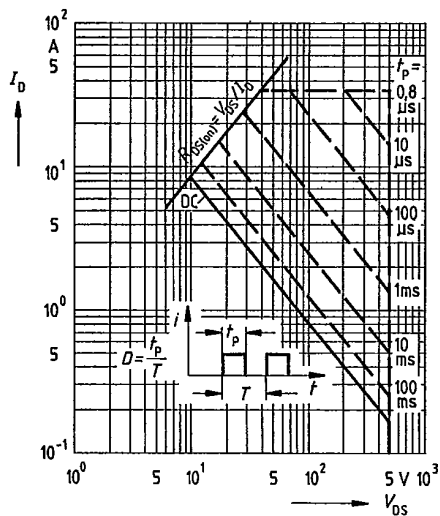
Power dissipation $P_D = f(T_C)$



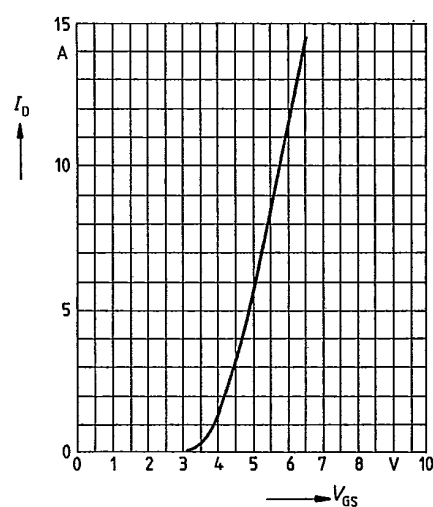
Typical output characteristics $I_D = f(V_{DS})$
parameter: 80 μ s pulse test,
 $T_1 = 25^\circ\text{C}$



Safe operating area $I_D = f(V_{DS})$
parameter: $D = 0.01$, $T_C = 25^\circ\text{C}$



Typical transfer characteristic $I_D = f(V_{GS})$
parameter: 80 μ s pulse test,
 $V_{DS} = 25\text{V}$, $T_1 = 25^\circ\text{C}$



88D D 8235605 0014915 1 SIEG

88D 14915

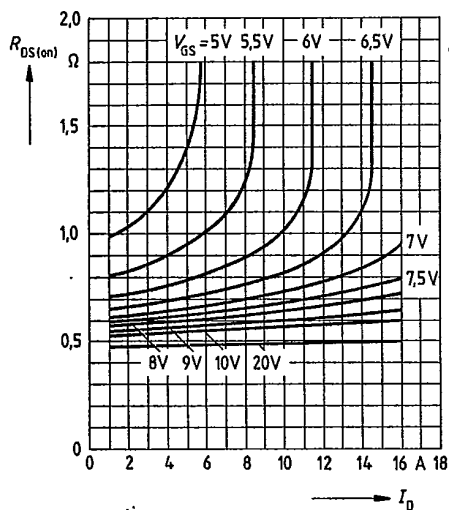
D T-39-13

BUZ 213

SIEMENS AKTIENGESellschaft

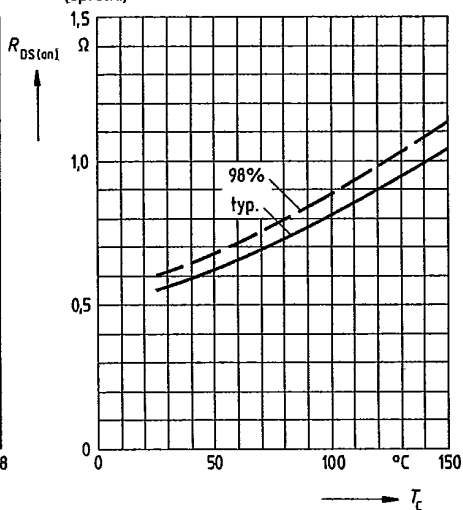
Typical drain-source on-state resistance

$R_{DS(on)} = f(I_D)$
parameter: $V_{GS} = 10V$, $T_j = 25^\circ C$



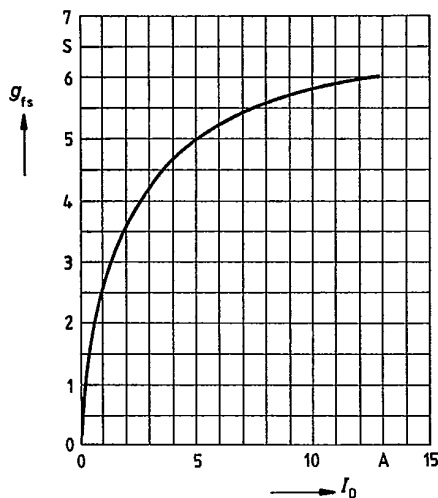
Drain-source on-state resistance

$R_{DS(on)} = f(T_j)$
parameter: $I_D = 5.5A$, $V_{GS} = 10V$
(spread)



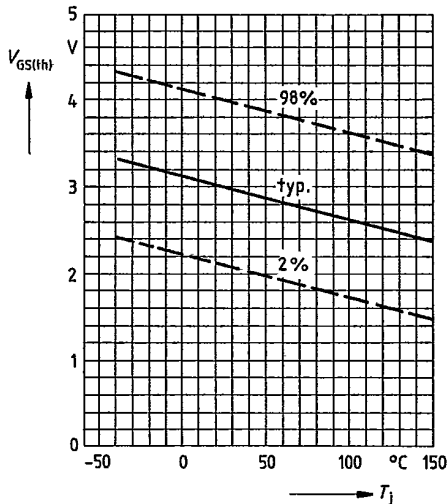
Typical transconductance $g_{fs} = f(I_D)$

parameter: 80 μs pulse test,
 $V_{DS} = 25V$, $T_j = 25^\circ C$



Gate threshold voltage $V_{GS(th)} = f(T_j)$

parameter: $V_{DS} = V_{GS}$, $I_D = 1mA$
(spread)



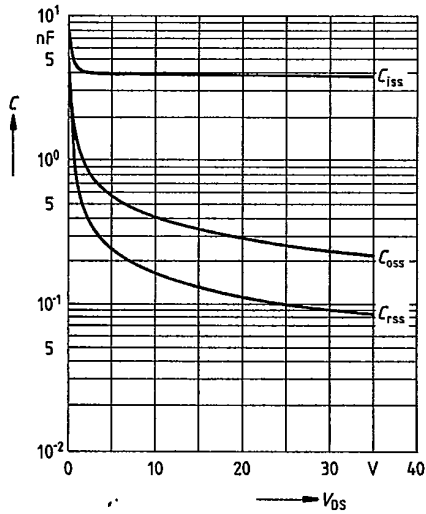
88D D 8235605 0014916 3 SIEG

88D 14916 D T-39-13

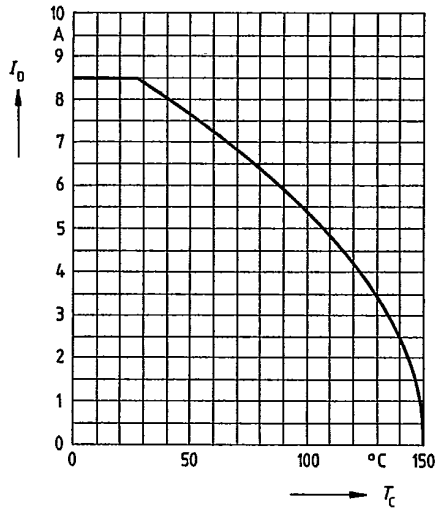
BUZ 213

— SIEMENS AKTIENGESSELLSCHAFT —

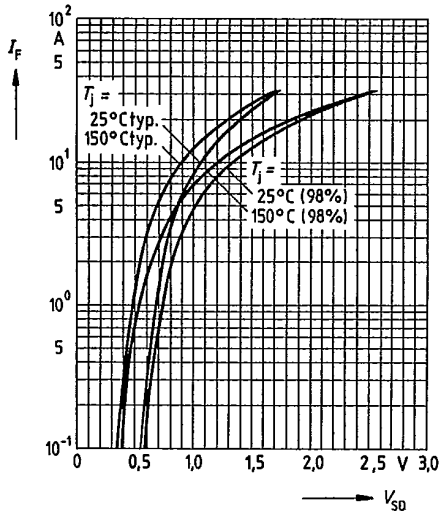
Typical capacitances $C = f(V_{DS})$
parameter: $V_{GS} = 0$, $f = 1\text{MHz}$



Continuous drain current $I_D = f(T_C)$
parameter: $V_{GS} \geq 10\text{V}$



Forward characteristic of reverse diode
 $I_F = f(V_{SD})$
parameter: T_j , $t_p = 80\text{ }\mu\text{s}$
(spread)



626

1208

B-13

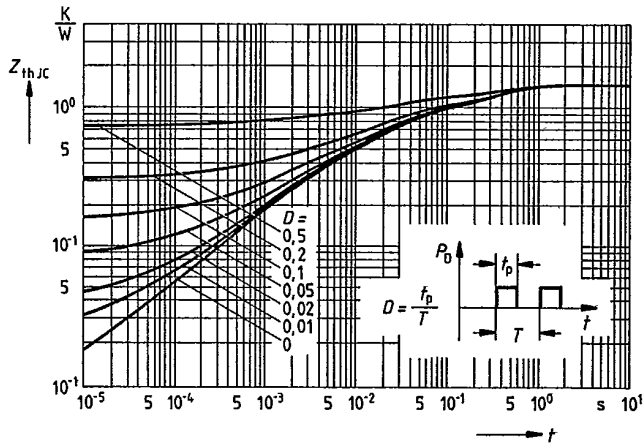
88D D 8235605 0014917 5 SIEG

88D 14917 D T-39-13

BUZ 213

SIEMENS AKTIENGESELLSCHAFT

Transient thermal impedance $Z_{thJC} = f(t)$
parameter: $D = t_p / T$



Typical gate-charge $V_{GS} = f(Q_{Gate})$
parameter: $I_{D\ puls} = 14,4A$

